



Patent Application 10772,940

Docket No. 2001-1300/24061.413  
Customer No. 42717

IFU

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Kuan-Lun Chang, et al.	§	Docket No.:	2001-1300 / 24061.413
		§		
Serial No.:	10/772,940	§	Examiner:	Quoc Dinh Hoang
		§		
Filed:	February 5, 2004	§	Art Unit:	2818
		§		
For:	Method of Forming a Shallow	§	Conf. No.:	6082
	Trench-Deep Trench Isolation	§		
	Region for a BiCMOS/CMOS	§		
	Technology	§		

**RESPONSE TO RESTRICTION REQUIREMENT**

Commissioner for Patents  
Mail Stop: Amendment  
PO Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

The present paper is being submitted in response to the Restriction Requirement Office Action dated August 9, 2005 in the above-identified application.

**Election of Claims** begins on page 2 of this paper.

**Amendments to the Claims** are reflected in the Listing of Claims which begins on page 3 of this paper.

**Remarks** begin on page 11 of this paper.

**I. Election**

In the Office Action mailed August 9, 2005, the Examiner alleges that the application contains claims directed to two inventions and, thus, required restriction of either:

Group I: Claims 29-35, drawn to a shallow trench-deep trench structure in a semiconductor substrate; or

Group II: Claims 1-28, drawn to a process of making an isolation region in semiconductor substrate.

In response, Applicants hereby elect Group II, corresponding to claims 1-28. Applicants' election is made with traverse on the grounds that the embodiments delineated by the Examiner are not patentably distinct and therefore constitute a single invention concept.